

Released

X-band Diode Limiter

Model No. NJS6930

Copyright©**Nisshinbo Micro Devices Inc.
Microwave Business Headquarters**

-Notice of Proprietary Information-

This document and its contents are proprietary to Nisshinbo Micro Devices Inc.
This publication and its contents may not be reproduced or distributed for any other purpose
without the written permission of Nisshinbo Micro Devices Inc.
Those specifications listed in this document are subject to change at any time.

■ GENERAL DESCRIPTION

NJS6930 is designed for the high power limiter of radar system.

It features a small size operable at any frequency between 9.30GHz and 9.50GHz.

This diode limiter consists of the two stage self-biased limiter diodes, and no external trigger and no bias are required.



■ ABSOLUTE MAXIMUM RATINGS

PARAMETERS	MINIMUM	MAXIMUM	UNITS
Maximum handling power (Fig.1)	-	8	kW
Continuous handling power (Fig.1)	-	4	kW
Ambient temperature	-30	+90	°C
RF pulse width (Fig.2)	-	-	μs

■ ELECTRICAL CHARACTERISTICS < at 25 °C >

PARAMETERS	MINIMUM	MAXIMUM	UNITS
V.S.W.R. (Note 1)	-	1.5	-
Insertion loss (Note 1,3)	-	1.5	dB
Flat leakage power (Note 2,3)	-	150	mW
Spike leakage power (Note 2,3)	-	600	mW
Recovery time (Note 2,3)	-	0.5	μs

Note 1: Measured at power level 0.1mW CW.

Note 2: Measured at power level 3kW, 1.0μs pulse width and 1000pps.

Note 3: Measured at frequency 9.40GHz.

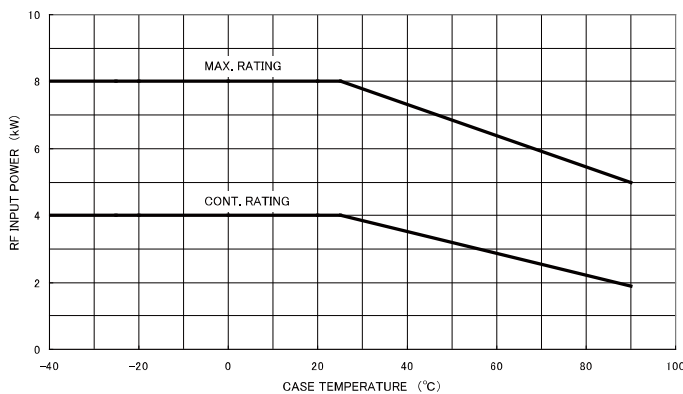


Fig.1 RF INPUT POWER MAXIMUM AND CONTINUOUS RATING (tp = 1 μs)

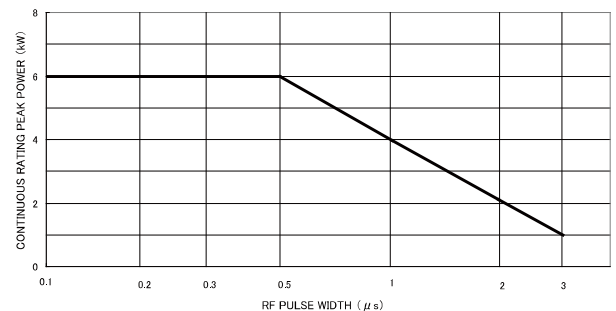
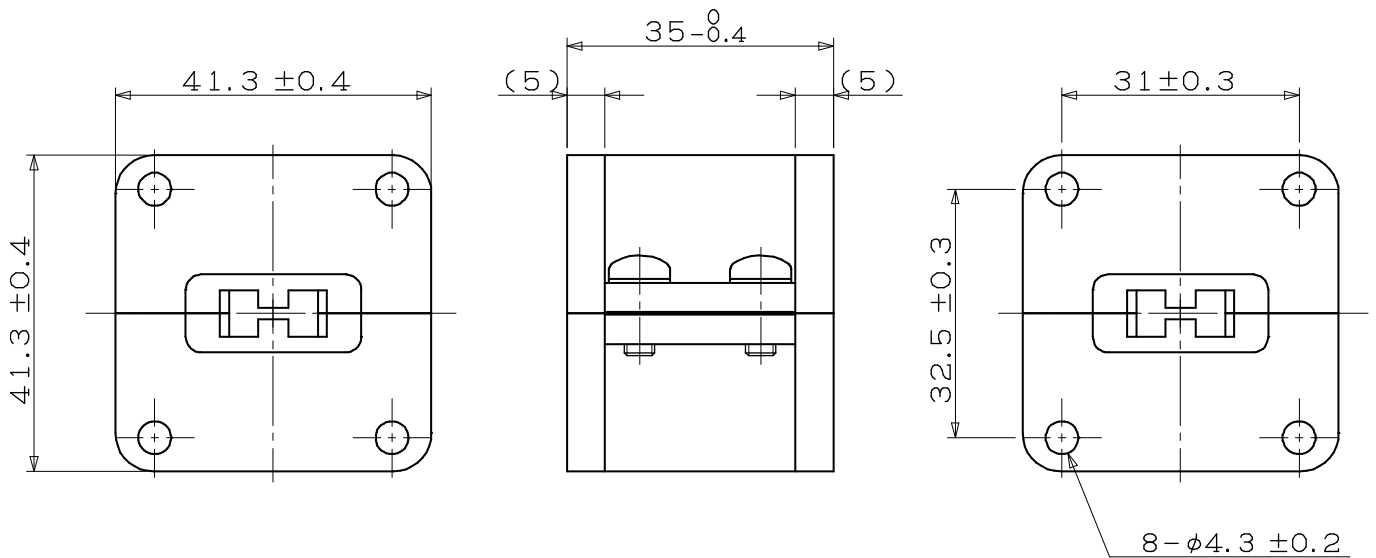
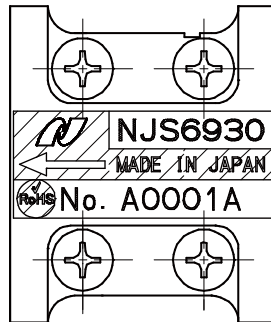


Fig.2 PULSE WIDTH DEPENDENCE OF CONTINUOUS RATING (at 25°C)

* Above Specifications are subject to change without notice.

■ OUTLINE



(Dimensions are expressed in "mm".)

* Above Specifications are subject to change without notice.

